

| L Number | Hits | Search Text | DB | Time stamp |
|----------|---------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------------------------------------|------------------|
| 1 | 2792480 | memory or storage | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/03/21 12:59 |
| 2 | 56 | (memory or storage) and (precharg\$5 or pre-charg\$5 or charg\$5) near3 (bit or bitline) and programmable with (resistor or resistance) | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/03/21 13:02 |
| 3 | 37 | ((memory or storage) and (precharg\$5 or pre-charg\$5 or charg\$5) near3 (bit or bitline) and programmable with (resistor or resistance)) and transistor with cell | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/03/21 13:03 |